NXP BUK9K17-60E MOSFET datasheet

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Dual logic level N-channel MOSFET in an LFPAK56D (Dual Power-SO8) package using TrenchMOS technology. This product has been designed and qualified to AEC Q101 standard for use in high performance automotive applications.

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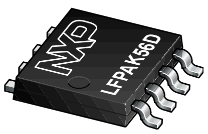

BUK9K17-60E

Dual N-channel 60 V, 17 mΩ logic level MOSFET

19 March 2014 — Product data sheet

1. General description

Dual logic level N-channel MOSFET in an LFPAK56D (Dual Power-SO8) package using TrenchMOS technology. This product has been designed and qualified to AEC Q101 standard for use in high performance automotive applications.

2. Features and benefits

- Dual MOSFET
- Q101 Compliant
- Repetitive avalanche rated
- Suitable for thermally demanding environments due to 175 °C rating
- True logic level gate with $V_{GS(th)}$ rating of greater than 0.5 V at 175 °C

3. Applications

- 12 V Automotive systems
- Motors, lamps and solenoid control
- Transmission control
- Ultra high performance power switching

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
V_{DS}	drain-source voltage	T_j ≥ 25 °C; T_j ≤ 175 °C		-	-	60	V
I_D	drain current	V_{GS} = 5 V; T_{mb} = 25 °C; Fig. 2	[1]	-	-	26	A
P_{tot}	total power dissipation	T_{mb} = 25 °C; Fig. 1		-	-	53	W
Static characteristics FET1 and FET2							
R_{DSon}	drain-source on-state resistance	V_{GS} = 5 V; I_D = 10 A; T_j = 25 °C; Fig. 11		-	14	17	mΩ
Dynamic characteristics FET1 and FET2							
Q_{GD}	gate-drain charge	I_D = 10 A; V_{DS} = 48 V; V_{GS} = 5 V; T_j = 25 °C; Fig. 13; Fig. 14		-	5.7	-	nC

[1] Continuous current is limited by package.

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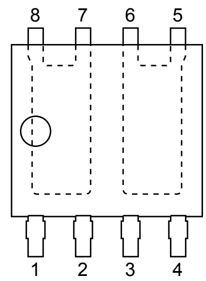
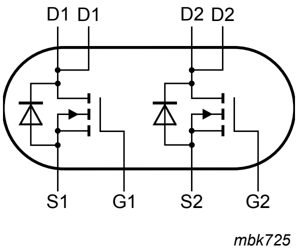
5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S1	source1	 LFPAK56D (SOT1205)	
2	G1	gate1		
3	S2	source2		
4	G2	gate2		
5	D2	drain2		
6	D2	drain2		
7	D1	drain1		
8	D1	drain1		

6. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BUK9K17-60E	LFPAK56D	Plastic single ended surface mounted package (LFPAK56D); 8 leads	SOT1205

7. Marking

Table 4. Marking codes

Type number	Marking code
BUK9K17-60E	91760E

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{DS}	drain-source voltage	$T_j \geq 25$ °C; $T_j \leq 175$ °C		-	60	V
V_{DGR}	drain-gate voltage	$R_{GS} = 20$ kΩ		-	60	V
V_{GS}	gate-source voltage	$T_j \leq 175$ °C; DC		-10	10	V
		$T_j \leq 175$ °C; Pulsed	[1][2]	-15	15	V
P_{tot}	total power dissipation	$T_{mb} = 25$ °C; Fig. 1		-	53	W
I_D	drain current	$T_{mb} = 25$ °C; $V_{GS} = 5$ V; Fig. 2	[3]	-	26	A
		$T_{mb} = 100$ °C; $V_{GS} = 5$ V; Fig. 2		-	26	A

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Symbol	Parameter	Conditions		Min	Max	Unit
I_{DM}	peak drain current	T_{mb} = 25 °C; pulsed; t_p ≤ 10 µs; Fig. 3		-	148	A
T_{stg}	storage temperature			-55	175	°C
T_j	junction temperature			-55	175	°C
Source-drain diode FET1 and FET2						
I_S	source current	T_{mb} = 25 °C	[3]	-	26	A
I_{SM}	peak source current	pulsed; t_p ≤ 10 µs; T_{mb} = 25 °C		-	148	A
Avalanche Ruggedness FET1 and FET2						
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	I_D = 26 A; V_{sup} ≤ 60 V; V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; Fig. 4	[4][5]	-	64	mJ

[1] Accumulated Pulse duration up to 50 hours delivers zero defect ppm
[2] Significantly longer life times are achieved by lowering T_j and or V_{GS}.
[3] Continuous current is limited by package.
[4] Refer to application note AN10273 for further information
[5] Single-pulse avalanche rating limited by maximum junction temperature of 175 °C

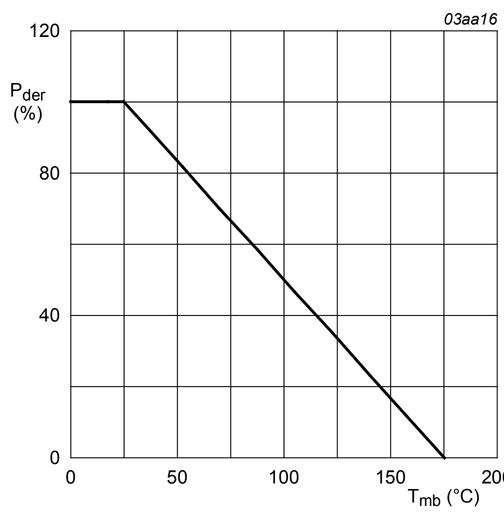

Fig. 1. Normalized total power dissipation as a function of mounting base temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^\circ C)}} \times 100\,\%$$

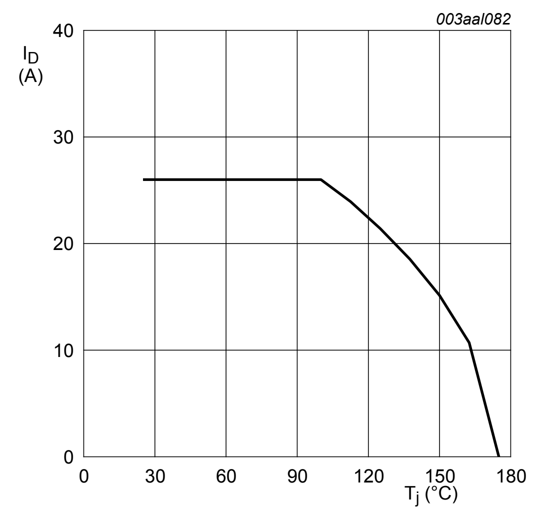

Fig. 2. Continuous drain current as a function of mounting base temperature

$$V_{GS} \geq 5V$$

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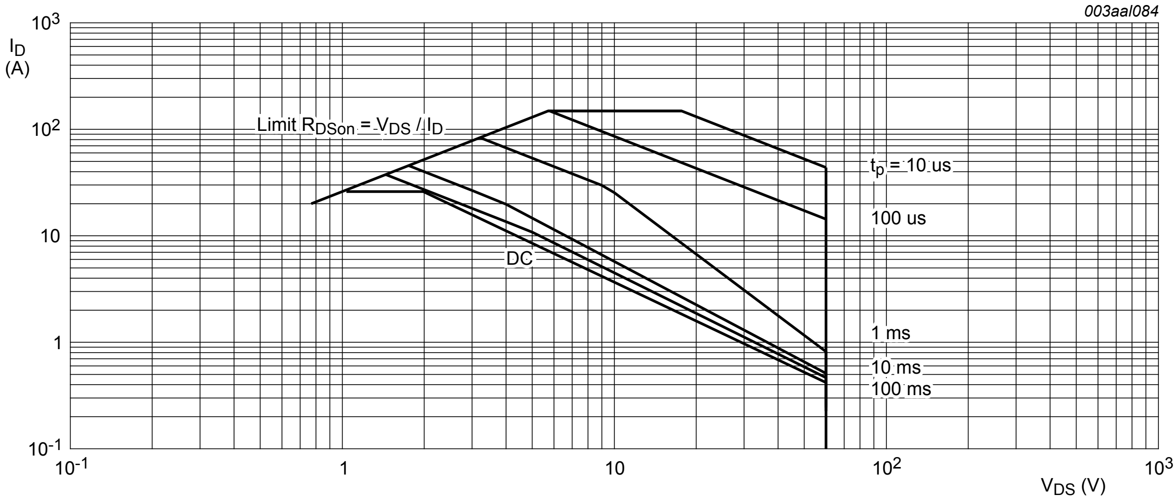

Fig. 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

$T_{mb} = 25°C$; I_{DM} is a single pulse

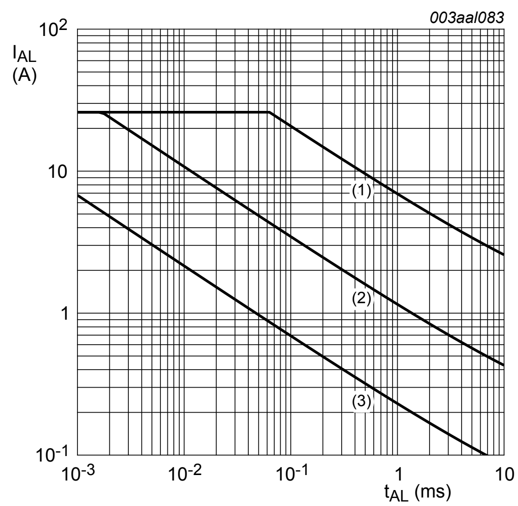

Fig. 4. Avalanche rating; avalanche current as a function of avalanche time

(1) $T_{j\,(init)} = 25°C$; (2) $T_{j\,(init)} = 150°C$; (3) Repetitive Avalanche

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	Fig. 5		-	-	2.84	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	Minimum footprint; mounted on a printed circuit board		-	95	-	K/W

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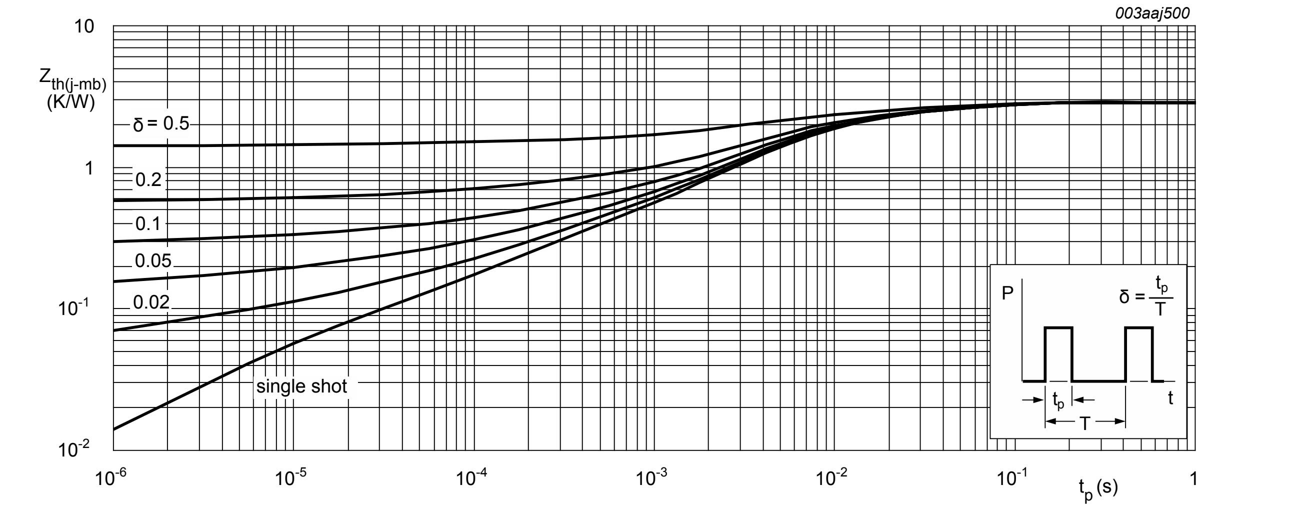

Fig. 5. Transient thermal impedance from junction to mounting base as a function of pulse duration.

10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
Static characteristics FET1 and FET2							
$V_{(BR)DSS}$	drain-source breakdown voltage	I_D = 250 µA; V_{GS} = 0 V; T_j = -55 °C		54	-	-	V
		I_D = 250 µA; V_{GS} = 0 V; T_j = 25 °C		60	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	I_D = 1 mA; V_{DS} = V_{GS}; T_j = 25 °C; Fig. 9; Fig. 10		1.4	1.7	2.1	V
		I_D = 1 mA; V_{DS} = V_{GS}; T_j = 175 °C; Fig. 9; Fig. 10		0.5	-	-	V
		I_D = 1 mA; V_{DS} = V_{GS}; T_j = -55 °C; Fig. 9; Fig. 10		-	-	2.45	V
I_{DSS}	drain leakage current	V_{DS} = 60 V; V_{GS} = 0 V; T_j = 25 °C		-	0.02	1	µA
		V_{DS} = 60 V; V_{GS} = 0 V; T_j = 175 °C		-	-	500	µA
I_{GSS}	gate leakage current	V_{GS} = -10 V; V_{DS} = 0 V; T_j = 25 °C		-	2	100	nA
		V_{GS} = 10 V; V_{DS} = 0 V; T_j = 25 °C		-	2	100	nA
R_{DSon}	drain-source on-state resistance	V_{GS} = 5 V; I_D = 10 A; T_j = 25 °C; Fig. 11		-	14	17	mΩ
		V_{GS} = 5 V; I_D = 10 A; T_j = 175 °C; Fig. 11; Fig. 12		-	31.6	38.4	mΩ
		V_{GS} = 10 V; I_D = 10 A; T_j = 25 °C; Fig. 11		-	12.4	15.6	mΩ
Dynamic characteristics FET1 and FET2							
$Q_{G(tot)}$	total gate charge	I_D = 10 A; V_{DS} = 48 V; V_{GS} = 5 V; T_j = 25 °C; Fig. 13; Fig. 14		-	16.5	-	nC
Q_{GS}	gate-source charge			-	3.3	-	nC

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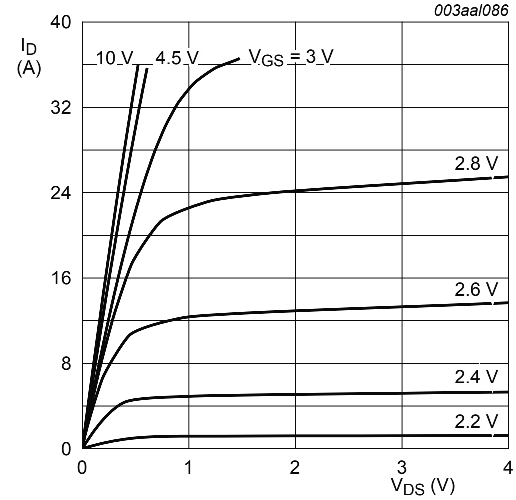
Symbol	Parameter	Conditions		Min	Typ	Max	Unit
Q_{GD}	gate-drain charge			-	5.7	-	nC
C_{iss}	input capacitance	V_{GS} = 0 V; V_{DS} = 25 V; f = 1 MHz; T_j = 25 °C; Fig. 15		-	1667	2223	pF
C_{oss}	output capacitance			-	160	193	pF
C_{rss}	reverse transfer capacitance	V_{GS} = 0 V; V_{DS} = 48 V; f = 1 MHz; T_j = 25 °C; Fig. 15		-	91	124	pF
$t_{d(on)}$	turn-on delay time	V_{DS} = 48 V; R_L = 5 Ω; V_{GS} = 5 V; $R_{G(ext)}$ = 5 Ω; T_j = 25 °C; I_D = 10 A		-	10.7	-	ns
t_r	rise time			-	20	-	ns
$t_{d(off)}$	turn-off delay time			-	23	-	ns
t_f	fall time			-	19.2	-	ns
Source-drain diode FET1 and FET2							
V_{SD}	source-drain voltage	I_S = 10 A; V_{GS} = 0 V; T_j = 25 °C; Fig. 16		-	0.78	1.2	V
t_{rr}	reverse recovery time	I_S = 10 A; dI_S/dt = -100 A/µs; V_{GS} = 0 V; V_{DS} = 30 V; T_j = 25 °C		-	20.3	-	ns
Q_r	recovered charge			-	16.7	-	nC



T_j = 25 °C; t_p = 300 µs

Fig. 6. Output characteristics; drain current as a function of drain-source voltage; typical values

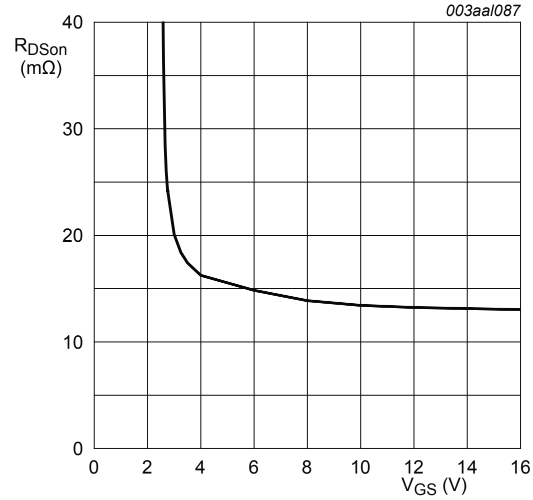


Fig. 7. Drain-source on-state resistance as a function of gate-source voltage; typical values

$T_j = 25°C;\ I_D = 10A$

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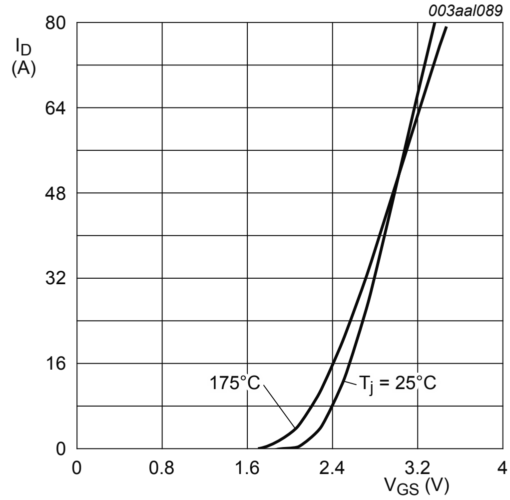


Fig. 8. Transfer characteristics; drain current as a function of gate-source voltage; typical values

$V_{DS} = 10V$

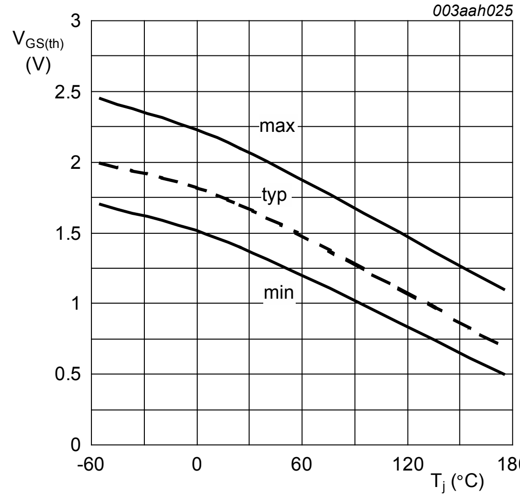


Fig. 9. Gate-source threshold voltage as a function of junction temperature

$I_D = 1$ mA; $V_{DS} = V_{GS}$

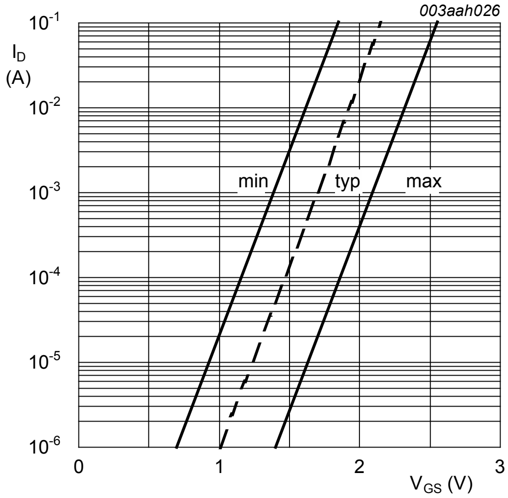
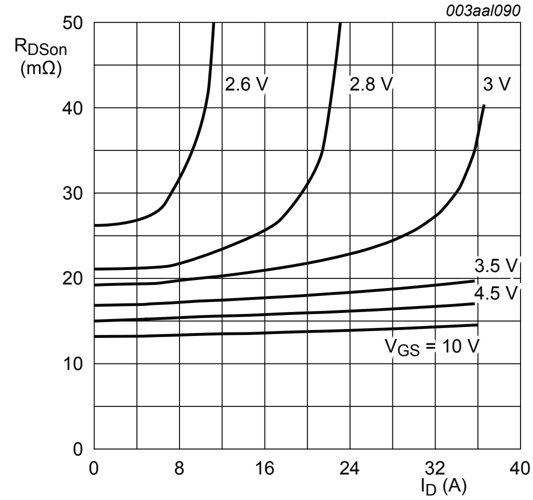


Fig. 10. Sub-threshold drain current as a function of gate-source voltage

$T_j = 25°C$; $V_{DS} = 5V$



$T_j = 25$ °C; $t_p = 300$ μs

Fig. 11. Drain-source on-state resistance as a function of drain current; typical values

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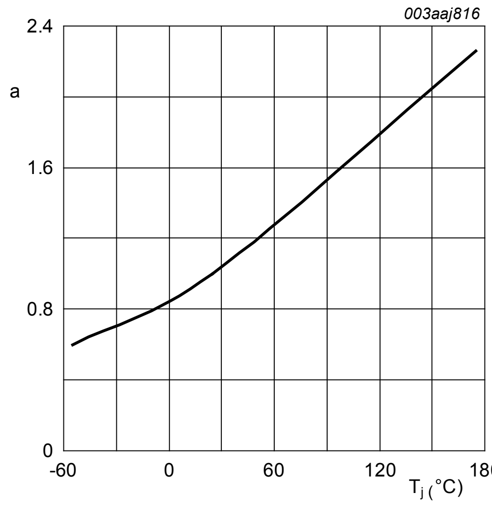

Fig. 12. Normalized drain-source on-state resistance factor as a function of junction temperature

$$a = \frac{R_{DSon}}{R_{DSon\,(25°C)}}$$

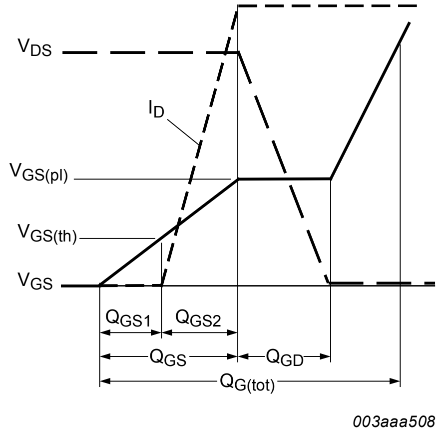

Fig. 13. Gate charge waveform definitions

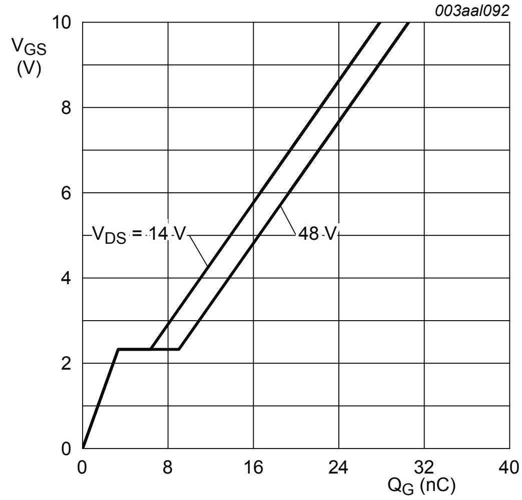

Fig. 14. Gate-source voltage as a function of gate charge; typical values

$T_j = 25°C;\ I_D = 10A$

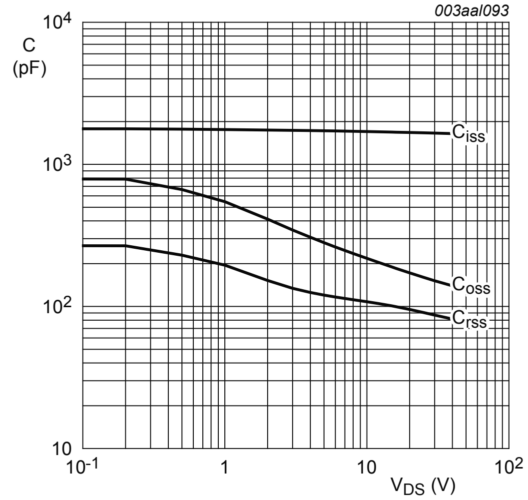

Fig. 15. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

$V_{GS} = 0V;\ f = 1MHz$

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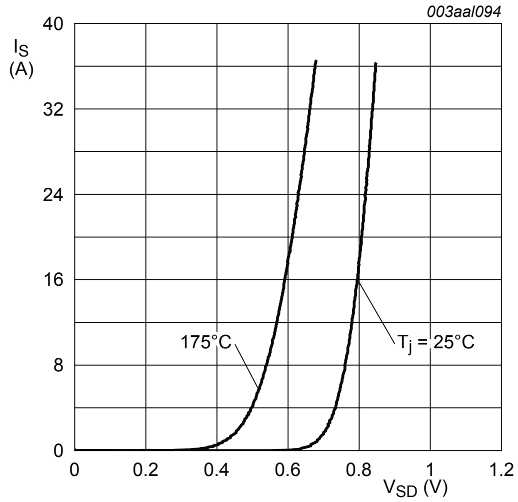

Fig. 16. Source (diode forward) current as a function of source-drain (diode forward) voltage; typical values

$V_{GS} = 0 V$

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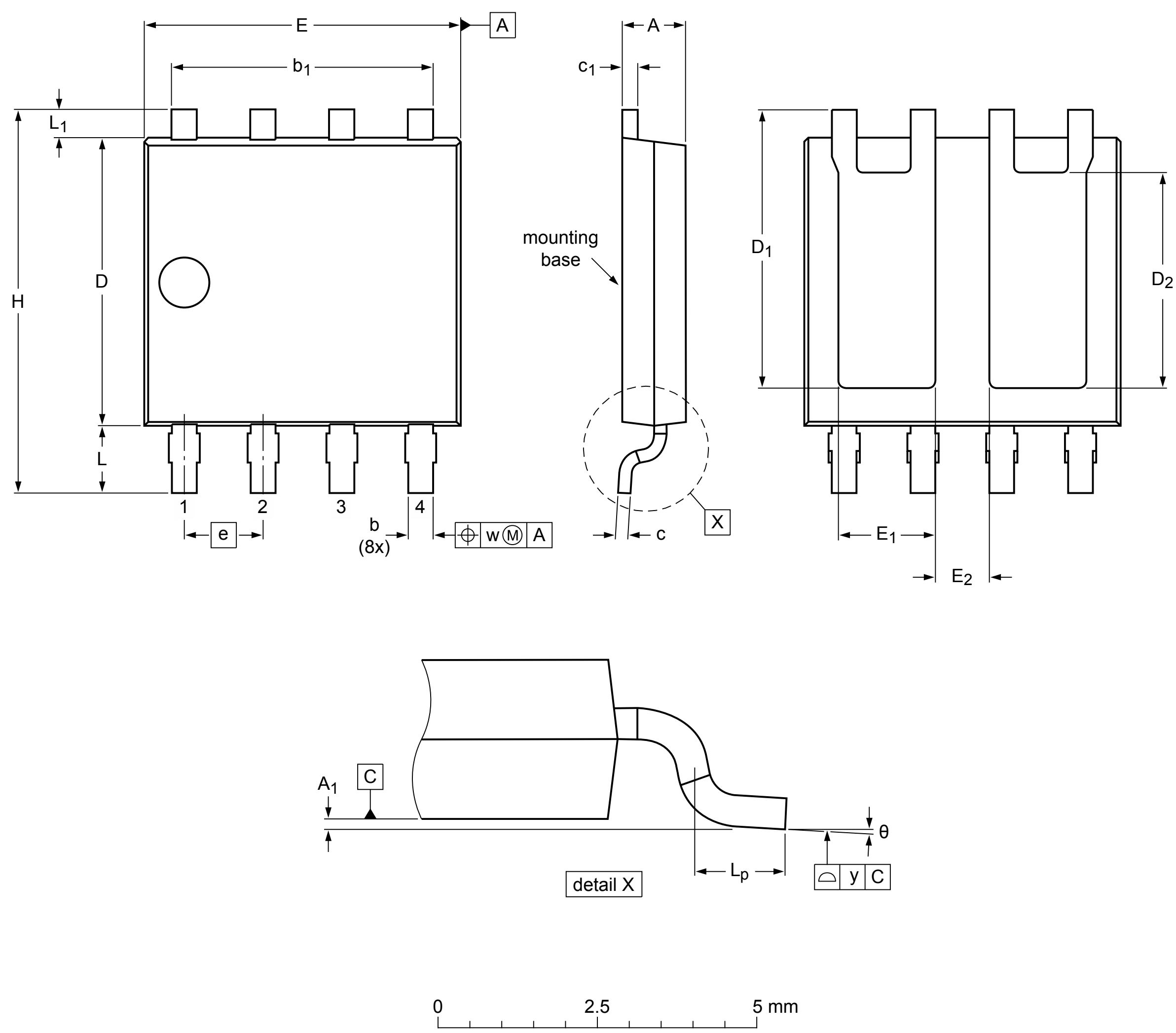
11. Package outline

Plastic single ended surface mounted package (LFPAK56D); 8 leads **SOT1205**



Dimensions

Unit		A	A_1	b	b_1	c	c_1	$D^{(1)}$	$D_1^{(1)}$	D_2 (ref)	$E^{(1)}$	$E_1^{(1)}$	E_2	e	H	L	L_1	L_p	w	y	θ
mm	max	1.05	0.1	0.50	4.4	0.25	0.30	4.70	4.8		5.30	1.8	0.85		6.2	1.3	0.55	0.85			8°
	nom									3.5				1.27					0.25	0.1	
	min		0.0	0.35	4.1	0.19	0.24	4.45			4.95	1.6			5.9	0.8	0.30	0.40			0°

Note

1. Plastic or metal protrusions of 0.2 mm maximum per side are not included.

sot1205_po

Outline version	References: IEC	References: JEDEC	References: JEITA		European projection	Issue date
SOT1205						~~13-02-19~~ 13-02-21

Fig. 17. Package outline LFPAK56D (SOT1205)

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12.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.
[2] The term 'short data sheet' is explained in section "Definitions".
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13. Contents

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Date of release: 19 March 2014

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